



GaAs InGaP HBT MMIC POWER AMPLIFIER, 0.8 - 1.0 GHz

Typical Applications

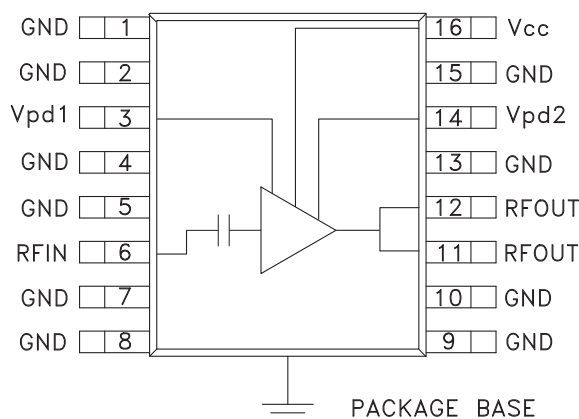
The HMC450QS16G / HMC450QS16GE is ideal for power and driver amplifier applications:

- GSM, GPRS, & Edge
- CDMA & WCDMA
- Base Stations & Repeaters

Features

- Gain: 26 dB
- 32% PAE @ 28.5 dBm Output Power
- +40 dBm Output IP3
- Integrated Power Control (Vpd)
- Included in the HMC-DK002 Designer's Kit

Functional Diagram



General Description

The HMC450QS16G & HMC450QS16GE are high efficiency GaAs InGaP HBT Medium Power MMIC amplifiers operating between 800 and 1000 MHz. The amplifier is packaged in a low cost, surface mount 16 lead package and offers the same pinout and functionality as the higher band HMC413QS16G 1.6-2.3 GHz PA. With a minimum of external components, the amplifier provides 26 dB of gain, +40 dBm OIP3 and +28.5 dBm of saturated power from a +5V supply voltage. The integrated power control (Vpd) can be used for full power down or RF output power/current control. The combination of high gain and high output IP3 make the HMC450QS16G & HMC450QS16GE ideal linear drivers for Cellular, PCS & 3G applications.

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_S = +5\text{V}$, $V_{pd} = +4\text{V}$ [1]

Parameter	Min.	Typ.	Max.	Units
Frequency Range	0.8 - 1.0			GHz
Gain	23	26		dB
Gain Variation Over Temperature		0.015	0.025	dB/°C
Input Return Loss		17		dB
Output Return Loss		13		dB
Output Power for 1 dB Compression (P1dB)	23	26		dBm
Saturated Output Power (Psat)		28.5		dBm
Output Third Order Intercept (IP3) [2]	37	40		dBm
Noise Figure		8		dB
Supply Current (Icq)		310		mA
Control Current (Ipd)		12		mA
Switching Speed	tON, tOFF	10		ns

[1] Specifications and data reflect HMC450QS16G measured using the application circuit found herein. Contact the HMC Applications Group for assistance in optimizing performance for your application.

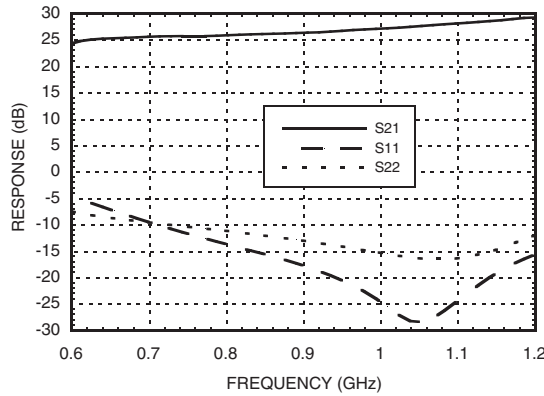
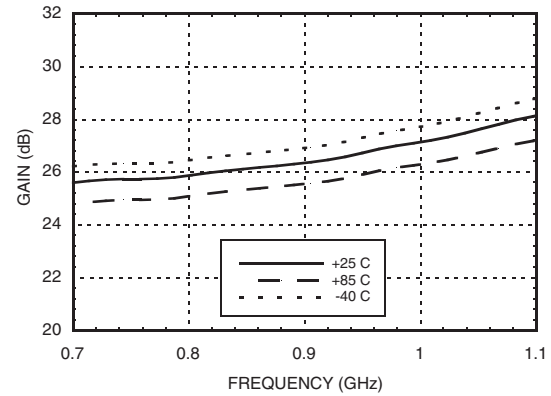
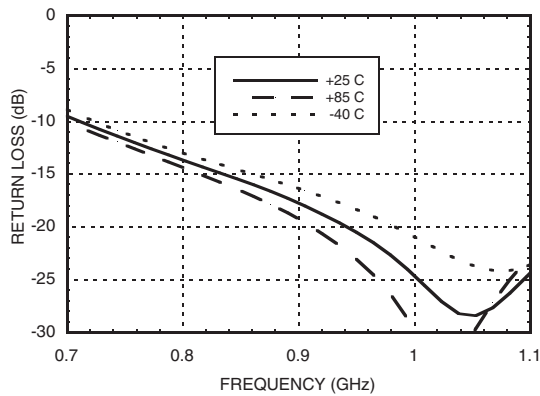
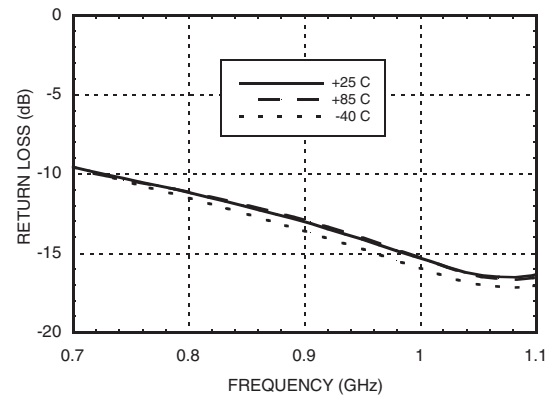
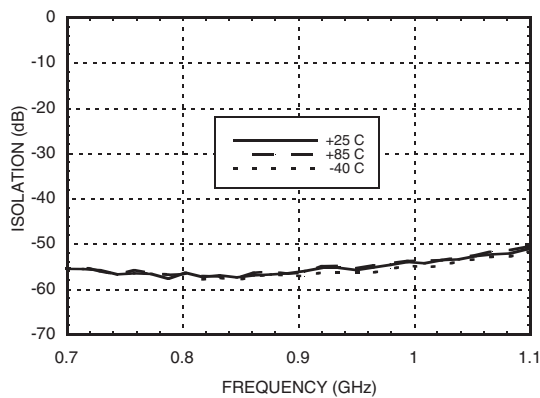
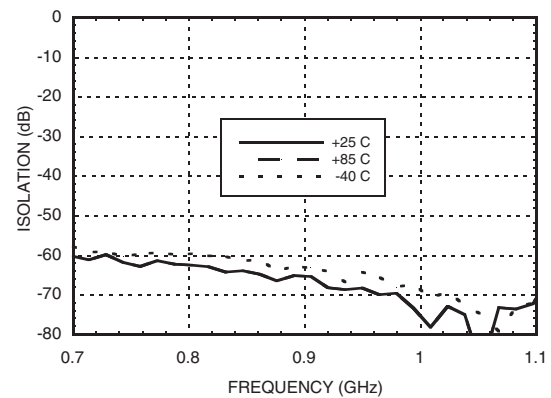
[2] Two-tone output power of +15 dBm per tone, 1 MHz spacing.

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

For price, delivery, and to place orders: Analog Devices, Inc., One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106
Phone: 781-329-4700 • Order online at www.analog.com
Application Support: Phone: 1-800-ANALOG-D



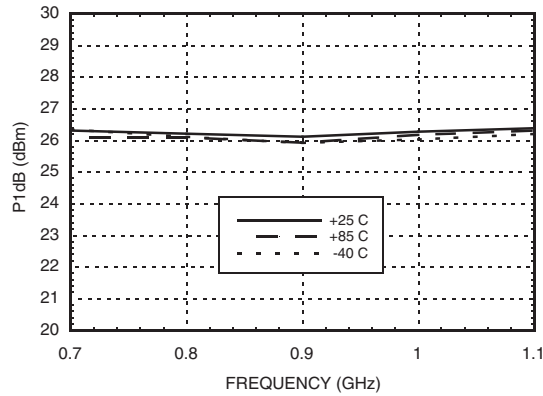
GaAs InGaP HBT MMIC POWER AMPLIFIER, 0.8 - 1.0 GHz

Broadband Gain & Return Loss

Gain vs. Temperature

Input Return Loss vs. Temperature

Output Return Loss vs. Temperature

Reverse Isolation vs. Temperature

Power Down Isolation vs. Temperature


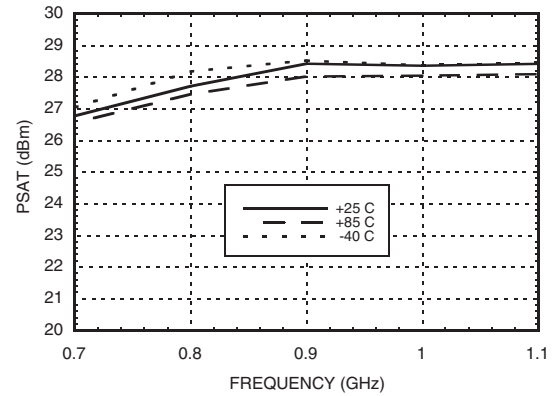


**GaAs InGaP HBT MMIC
POWER AMPLIFIER, 0.8 - 1.0 GHz**

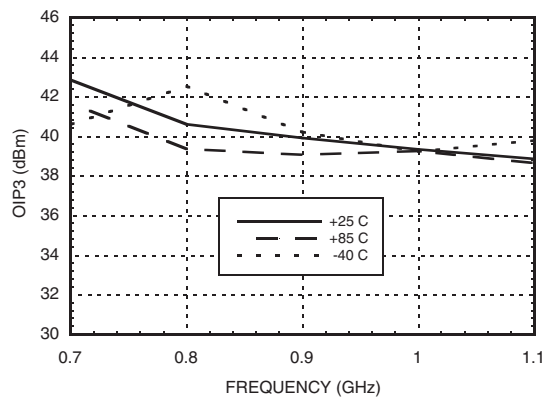
P1dB vs. Temperature



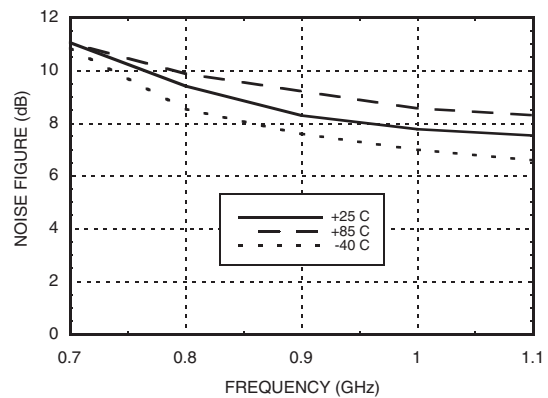
Psat vs. Temperature



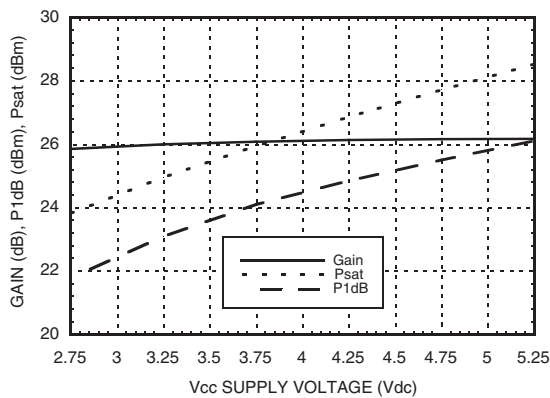
Output IP3 vs. Temperature



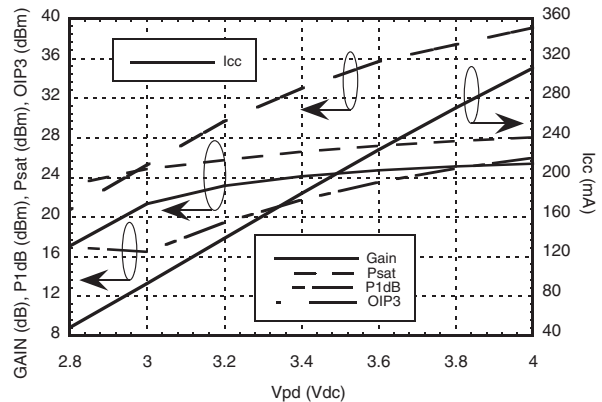
Noise Figure vs. Temperature



**Gain and Power vs.
Supply Voltage @ 900 MHz, Vpd= 4V**



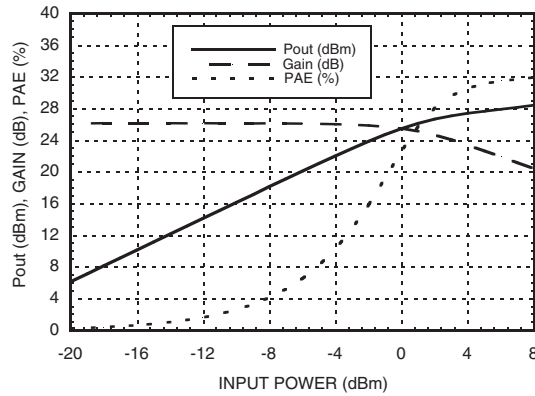
**Gain, Power, OIP3 and Supply Current
vs. Power Down Voltage @ 900 MHz**



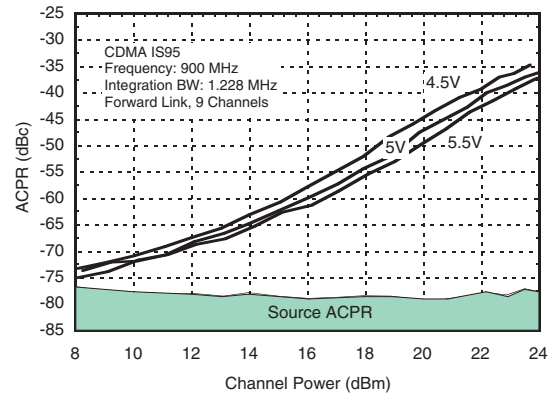


**GaAs InGaP HBT MMIC
POWER AMPLIFIER, 0.8 - 1.0 GHz**

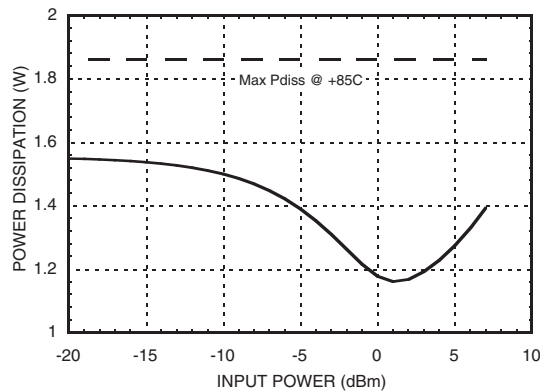
Power Compression @ 900 MHz



**ACPR vs. Supply Voltage @ 900 MHz
CDMA IS95, 9 Channels Forward**



Power Dissipation @ 900 MHz




**GaAs InGaP HBT MMIC
POWER AMPLIFIER, 0.8 - 1.0 GHz**
**Typical Supply Current
vs. Supply Voltage**

Vs (V)	Icq (mA)
4.75	300
5.0	310
5.25	325

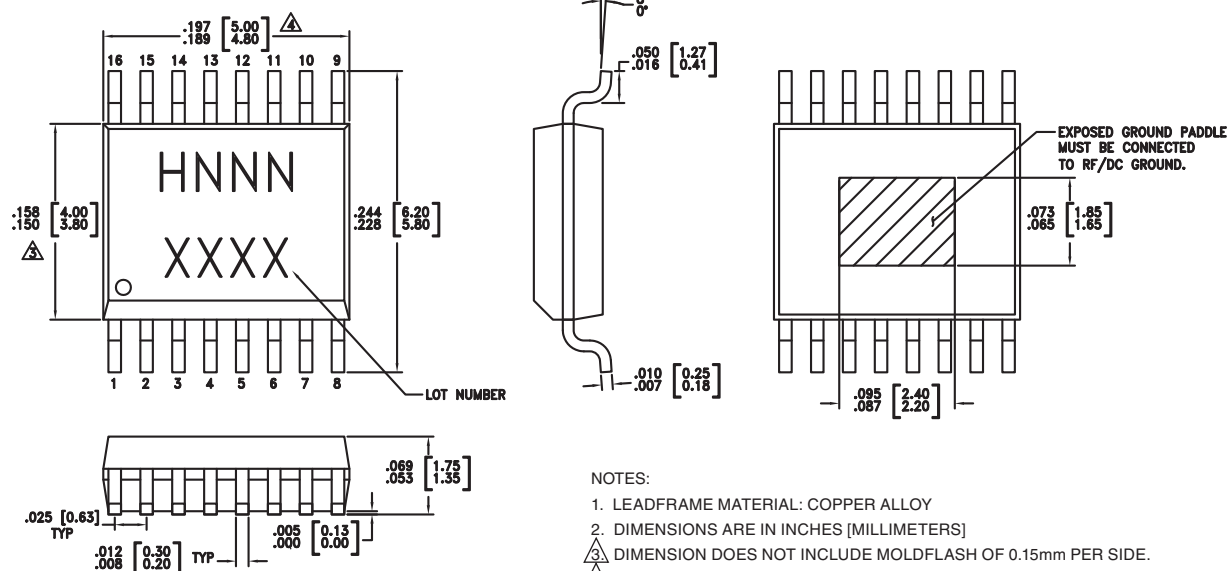
Note: Amplifier will operate over full voltage range shown above



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

Absolute Maximum Ratings

Collector Bias Voltage (Vcc)	+5.5 Vdc
Control Voltage (Vpd1, Vpd2)	+5Vdc
RF Input Power (RFIN)(Vs = +5Vdc, VPD = +4.0 Vdc)	+10 dBm
Junction Temperature	150 °C
Continuous Pdis (T = 85 °C) (derate 28 mW/°C above 85 °C)	1.86 W
Thermal Resistance (junction to ground paddle)	35 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

Outline Drawing

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC450QS16G	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H450 XXXX
HMC450QS16GE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H450 XXXX

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

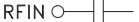
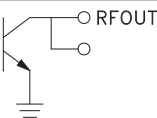
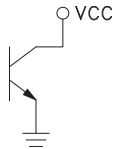
Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

For price, delivery, and to place orders: Analog Devices, Inc., One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106 Phone: 781-329-4700 • Order online at www.analog.com Application Support: Phone: 1-800-ANALOG-D



GaAs InGaP HBT MMIC POWER AMPLIFIER, 0.8 - 1.0 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4, 5, 7, 8, 9, 10, 13, 15	GND	Ground: Backside of package has exposed metal ground slug that must be connected to ground thru a short path. Vias under the device are required.	
3, 14	Vpd1, Vpd2	Power Control Pin. For maximum power, this pin should be connected to 4.0V. For 5V operation, a dropping resistor is required. A higher voltage is not recommended. For lower idle current, this voltage can be reduced.	
6	RFIN	This pin is AC coupled and matched to 50 Ohms from 0.8 to 1.0 GHz.	
11, 12	RFOUT	RF output and bias for the output stage.	
16	Vcc	Power supply voltage for the first amplifier stage. An external bypass capacitor of 330 pF is required as shown in the application schematic.	

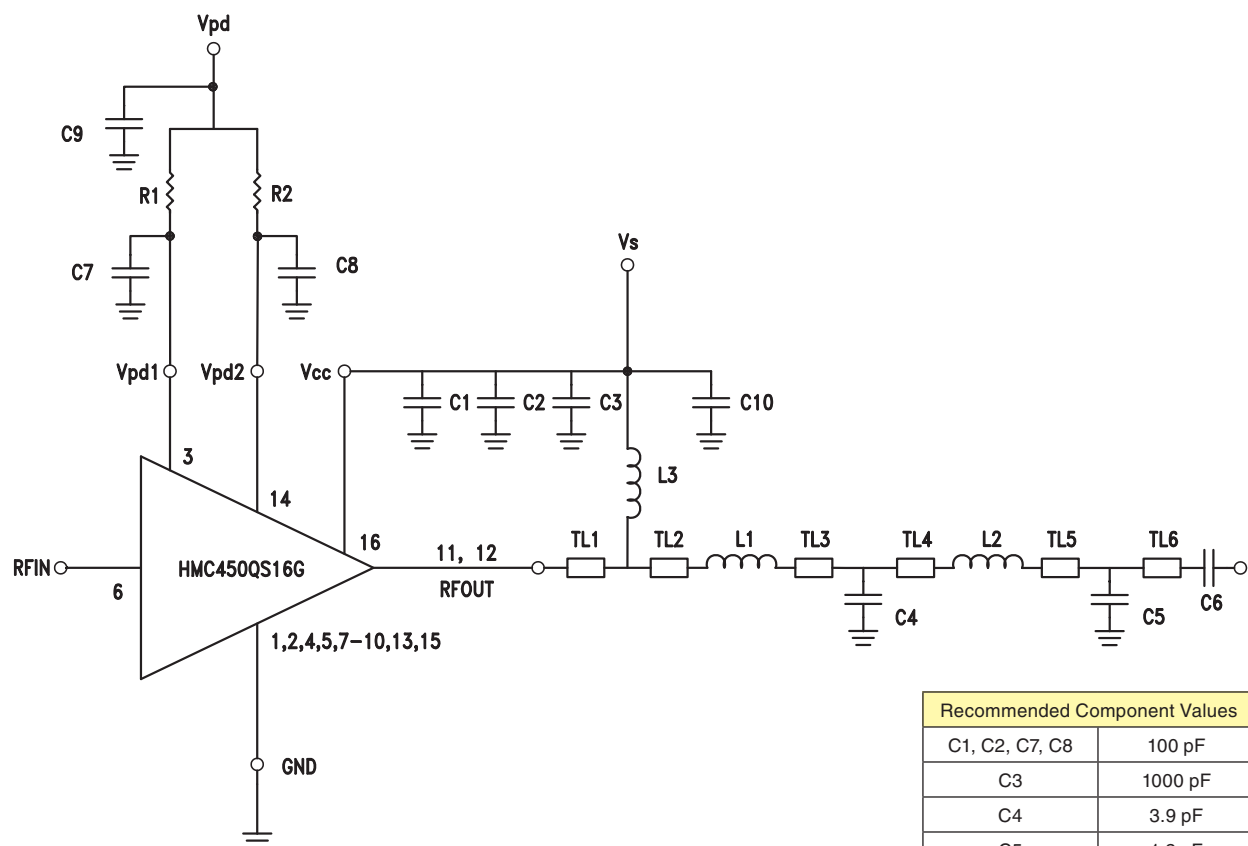
11

LINEAR & POWER AMPLIFIERS - SMT



**GaAs InGaP HBT MMIC
POWER AMPLIFIER, 0.8 - 1.0 GHz**

Application Circuit



Recommended Component Values	
C1, C2, C7, C8	100 pF
C3	1000 pF
C4	3.9 pF
C5	1.2 pF
C6	27 pF
C9, C10	2.2 μ F
L1	1.9 nH
L2	1.0 nH
L3	56 nH
R1, R2	50 Ohms

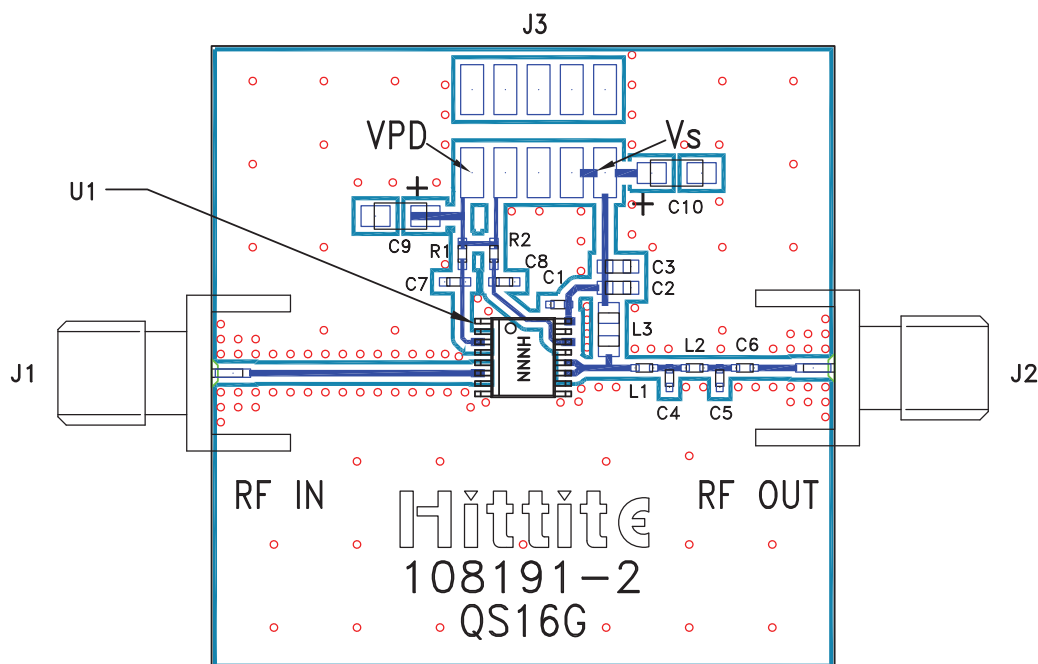
		TL1	TL2	TL3	TL4	TL5	TL6
	Impedance	50 Ohm	50 Ohm	50 Ohm	50 Ohm	50 Ohm	50 Ohm
Physical	Length	0.08"	0.05"	0.02"	0.02"	0.02"	0.02"
Electrical	Length	4'	2.5'	1.02'	1.02'	1.02'	1.02'

PCB Material: 10 mil Rogers 4350 Er = 3.48



**GaAs InGaP HBT MMIC
POWER AMPLIFIER, 0.8 - 1.0 GHz**

Evaluation PCB



List of Materials for Evaluation PCB 108349 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3	2 mm DC Header
C1, C7, C8	100 pF Capacitor, 0402 Pkg.
C2	100 pF Capacitor, 0603 Pkg.
C3	1000 pF Capacitor, 0603 Pkg.
C4	3.9 pF Capacitor, 0402 Pkg.
C5	1.2 pF Capacitor, 0402 Pkg.
C6	27 pF Capacitor, 0402 Pkg.
C9, C10	2.2 uF Capacitor, Tantalum
L1	1.9 nH Inductor 0402 Pkg.
L2	1.0 nH Inductor, 0402 Pkg.
L3	56nH Inductor, 0805 Pkg.
R1, R2	50 Ohms Resistor, 0402 Pkg.
U1	HMC450QS16G / HMC450QS16GE Power Amp.
PCB [2]	108191 Evaluation PCB, 10 mils

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru

www.lifeelectronics.ru